METHOD FOR MANUFACTURING A SILICON SURFACE WITH PYRAMIDAL STRUCTURE

Abstract

The invention relates to a method for manufacturing a silicon surface with a pyramidal structure, in which a silicon wafer containing the silicon surface is dipped into an etching solution. To produce a pyramidal structure that is as homogeneous as possible, according to the invention it is proposed that the silicon surface be treated with ozone prior to coming into contact with the etching solution.

[No suitable figure]